

IN THE CLAIMS

In accordance with 37 CFR 1.173 and MPEP § 1453, Please amend the claims as follows:

Claim 33: The semiconductor device manufacturing method according to claim 1, wherein the first conductivity-type region includes plural portions, the second conductivity-type region includes plural portions, and the plural portions of the first conductivity-type region are alternatively arranged with the plural portions of the second conductivity-type region and vertically to the surface of the semiconductor substrate.

Claim 34: The semiconductor device manufacturing method according to claim 2, wherein the cross-sectional shape and cross-section area of said first and second conductivity-type regions on planes perpendicular to the direction of irradiation are uniform in the direction of irradiation.

Claim 35: The semiconductor device manufacturing method according to claim 2, wherein the first conductivity-type region includes plural portions, the second conductivity-type region includes plural portions, and the plural portions of the first conductivity-type region are alternatively arranged with the plural portions of the second conductivity-type region and vertically to the surface of the semiconductor substrate.

Claim 36: The semiconductor device manufacturing method according to claim 12, wherein the cross-sectional shape and cross-section area of said first and second conductivity-type regions on planes perpendicular to the direction of irradiation are uniform in the direction of irradiation.

Claim 37: The semiconductor device manufacturing method according to claim 12, wherein the first conductivity-type region includes plural portions, the second conductivity-type region includes plural portions, and the plural portions of the first conductivity-type region are alternatively arranged with the plural portions of the second conductivity-type region and vertically to the surface of the semiconductor substrate.